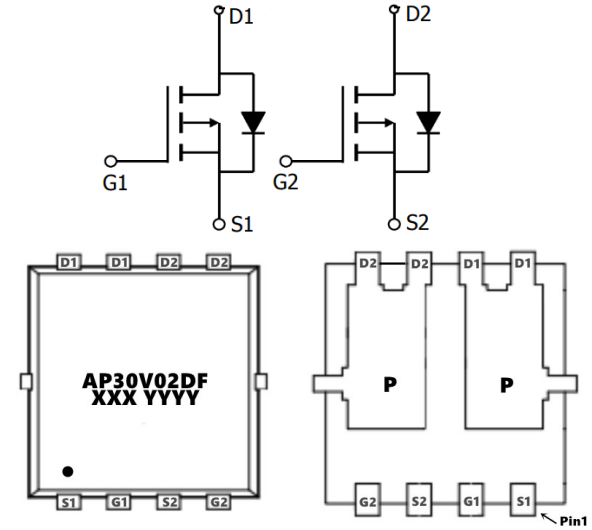
AP30V02DF

-20V P+P-Channel Enhancement Mode MOSFET

Description

The AP30V02DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = -20V I_D =-30A

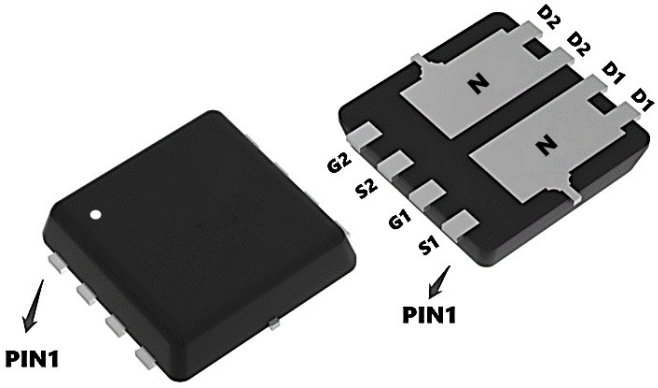
$R_{DS(ON)}$ < 16mΩ @ V_{GS}=4.5V（**Type：12.5mΩ**）

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30V02DF	PDFN3*3-8L	AP30V02DF XXX YYYY	5000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-30	A
I_D@T_A=70℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-19	A
I_{DM}	Pulsed Drain Current[2]	-90	A
P_D@T_A=25℃	Total Power Dissipation[4]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	85	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	12	℃/W

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Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	-23	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.012	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V , I_D=-20A	---	12.5	16	mΩ
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-2.5V , I_D=-10A	---	16.5	28	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.5	0.6	-1.2	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.94	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	1	uA
IGSS	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-6A	---	15.3	---	nC
Qgs	Gate-Source Charge		---	2.2	---	
Qgd	Gate-Drain Charge		---	4.4	---	
Td(on)	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω, I_D=-10A	---	10	---	ns
T_r	Rise Time		---	31	---	
Td(off)	Turn-Off Delay Time		---	28	---	
T_f	Fall Time		---	8	---	
Ciss	Input Capacitance	V_{DS}=-10V , V_{GS}=0V , f=1MHz	---	2000	---	pF
Coss	Output Capacitance		---	242	---	
Crss	Reverse Transfer Capacitance		---	231	---	
IS	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-20	A
ISM	Pulsed Source Current[2,4]		---	---	-48	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

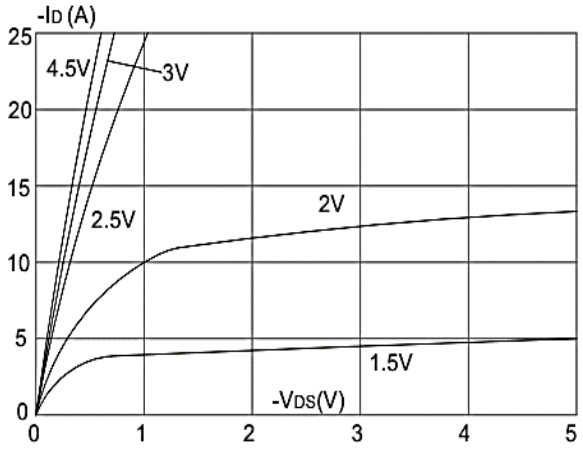


Figure1: Output Characteristics

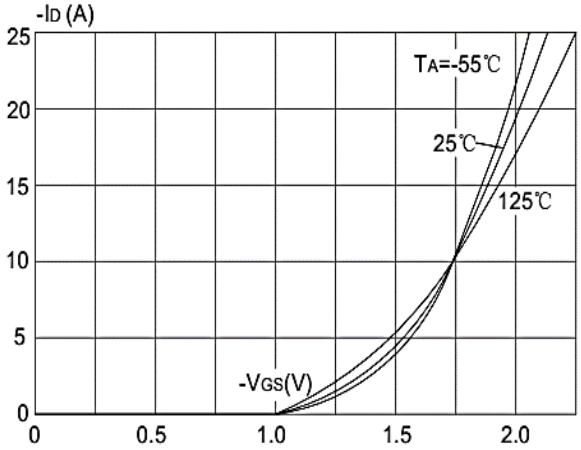


Figure 2: Typical Transfer Characteristics

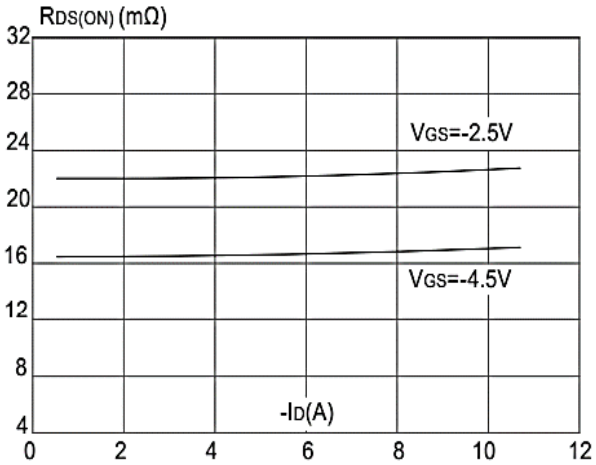


Figure 3:On-resistance vs. Drain Current

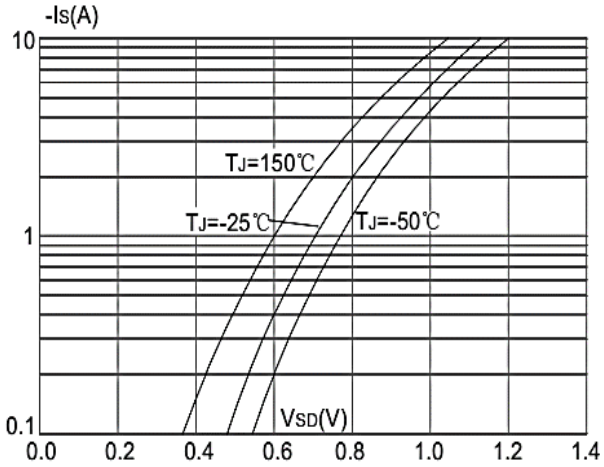


Figure 4: Body Diode Characteristics

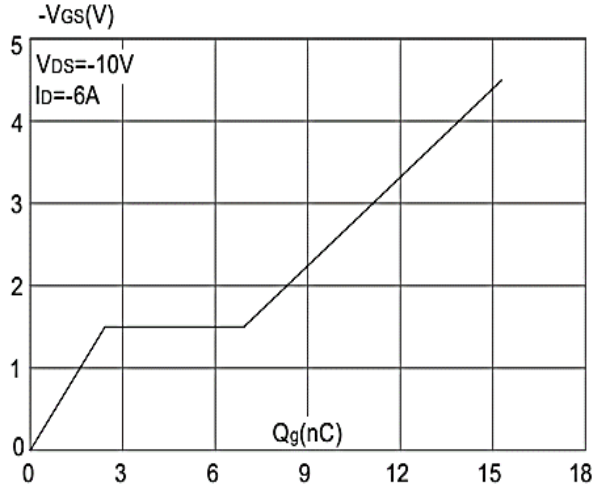


Figure 5: Gate Charge Characteristics

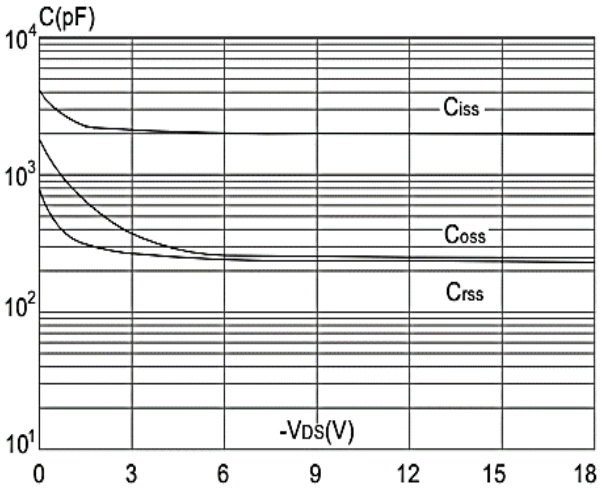


Figure 6: Capacitance Characteristics

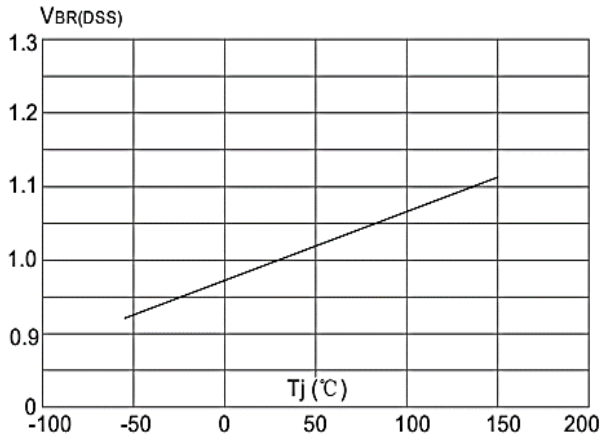


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

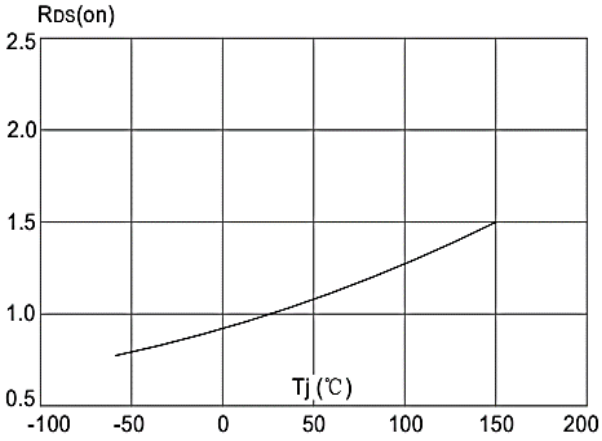


Figure 8: Normalized on Resistance vs. Junction Temperature

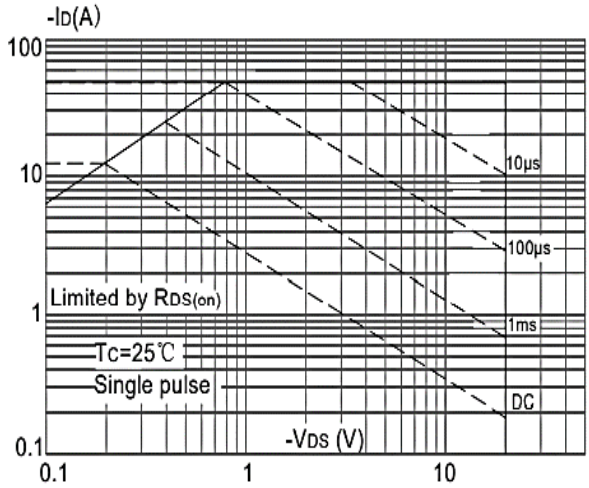


Figure 9: Maximum Safe Operating Area

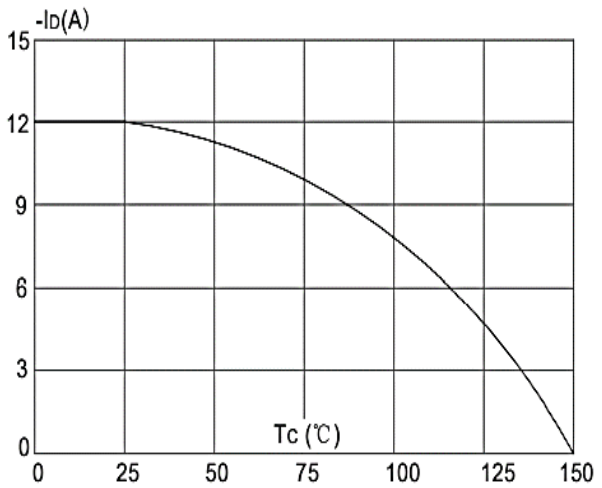


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

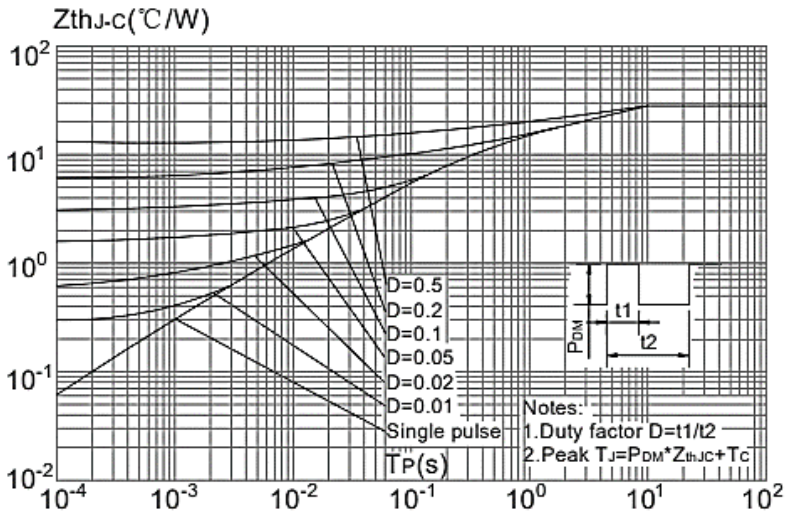
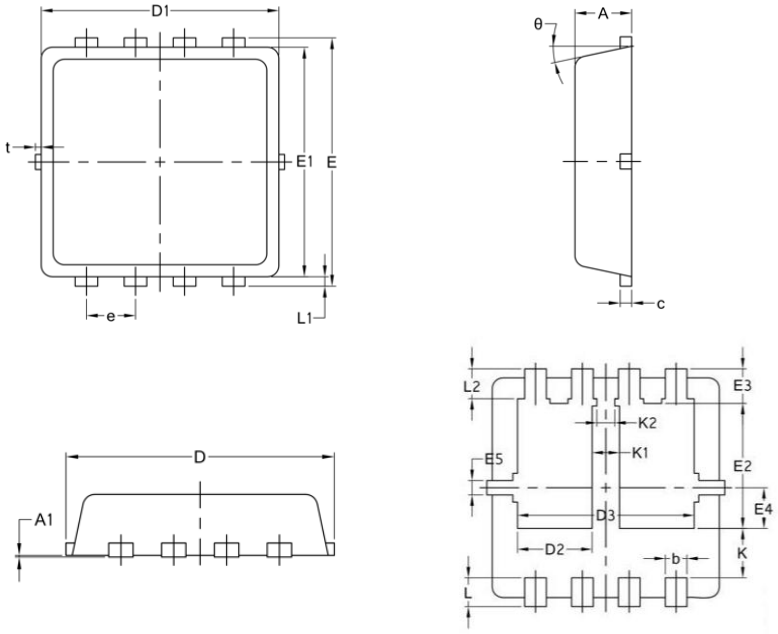


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

Package Mechanical Data-PDFN3*3-8L Double



Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°